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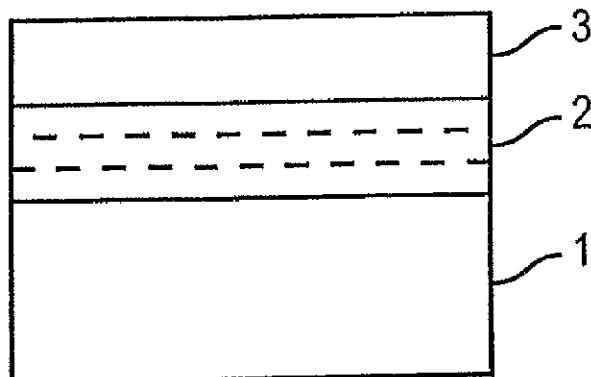
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(54) Title: SUBSTRATE HAVING A CHARGED ZONE IN AN INSULATING BURIED LAYER

FIG. 3

(57) Abstract: The invention relates to a substrate comprising successively a base wafer (1), an insulating layer (2) and a top semiconductor layer (3), characterised in that the insulating layer (2) comprises at least a zone wherein the density of charges is in absolute value higher than 10^{10} charges/cm². The invention also relates to a process for making such a substrate.



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